

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7313	438/105,145,625,627,643,758,778,780,787,789,931.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/17 09:47
L2	512	1 and (((silicon near carbide) SiC) near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/17 10:10
L3	19	2 and (oxygen near dop\$3 near ((silicon near carbide) SiC) near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/17 09:58
L4	0	1 and (((lower bottom) near (silicon near carbide) SiC) near (layer film)) with ((upper top) near oxygen near dop\$3 near ((silicon near carbide) SiC) near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/17 10:11
L5	0	1 and (((lower bottom) near (silicon near carbide) SiC)) with ((upper top) near oxygen near dop\$3 near ((silicon near carbide) SiC))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/17 10:11
L6	0	1 and (((lower bottom) near (silicon near carbide) SiC)) and ((upper top) near oxygen near dop\$3 near ((silicon near carbide) SiC))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/17 10:12
L7	3	(((lower bottom) near (silicon near carbide) SiC)) and ((upper top) near oxygen near dop\$3 near ((silicon near carbide) SiC))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/17 10:15
L8	1	((lower bottom) near ((silicon near carbide) SiC)) and ((upper top) near oxygen near dop\$3 near ((silicon near carbide) SiC))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/17 10:17

L9	1	damascene AND (method process\$3) AND substrate AND ((lower bottom) near ((silicon near carbide) SiC)) AND ((upper top) near oxygen near dop\$3 near ((silicon near carbide) SiC)) AND (first near dielectric) AND open\$3 AND (sidewall\$1 (side near wall\$1)) AND bottom AND (diffus\$3 near barrier) AND (metal conduct\$3) AND fill\$3.CLM.	US-PGPUB; USPAT	OR	ON	2006/01/17 10:21
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